## Pressure effect on the charge-density-wave formation in 2H-NbSe<sub>2</sub> and correlation between structural instabilities and superconductivity in unstable solids

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The hydrostatic pressure dependence of the charge-density-wave onset temperature  $T_0$  in 2H-NbSe $_2$  was measured up to 20 kbar.  $dT_0/dP$  was found to be  $-(3.3\pm0.2)\times10^{-4}$  K bar $^{-1}$ . An examination of existing high-pressure data concerning structural instabilities and superconductivity in both layered and isotropic compounds is made.

2H-NbSe, is a trigonal prismatic coordinated layer compound. On cooling, it undergoes a structural transition at the onset temperature  $T_0 = 32 \text{ K}$ of a incommensurate charge-density-wave (CDW) state<sup>2</sup> and becomes superconducting below ~7.2 K.<sup>3</sup> The superconducting transition temperature  $T_0$  of 2H-NbSe2 increases rapidly and nonlinearly with pressure up to ~35 kbar, but slowly and linearly beyond ~35 kbar.4 This pressure-enhanced superconductivity has been ascribed to the possible suppression of the structural transition by pressure<sup>5</sup> or to the band broadening due to pressure-promoted interlayer coupling4 (it seems possible that the two are related). Our direct pressure measurements on  $T_0$  show that  $T_0$  decreases with pressure. However, recent results on 2H-TaSe2 show that pressure increases  $T_0$ , and also  $T_c$ .

Measurements have been made of the pressure dependences of  $T_0$  and  $T_c$  of 2H-NbSe<sub>2</sub> in the fluid mixture of 1:1 n-pentane and isoamyl alcohol, using a self-clamp technique. A sample with a resistance ratio of 30 along the layer between 300 and 8 K was cut from a single crystal grown by iodine chemical vapor transport technique.  $T_0$  is defined as the temperature where the resistance vs temperature curve exhibits a point of inflection.  $T_0$  so defined is slightly lower than that previously obtained<sup>8</sup> at P = 1 bar, but gives less uncertainty in determining  $T_0$  at higher pressure.  $T_c$  was measured both resistively and inductively. Results are shown in Fig. 1, with the number indicating the sequential order of the experimental runs. The vertical bar for  $T_0$  represents the uncertainty in locating  $T_{\rm o}$  and that for  $T_{\rm c}$  the transition width.  $T_{\rm 0}$  decreases linearly with pressure up to 20 kbar at a rate of  $-(3.3 \pm 0.2) \times 10^{-4}$  Kbar<sup>-1</sup>. Tc increases with pressure but with a negative

curvature. Both  $T_c$  and  $dT_c/dp$  apparently depend on the measuring technique used, possibly due to the anisotropic nature of the compounds. At atmospheric pressure,  $dT_c/dp = + (5.2 \pm 0.1) \times 10^{-5}$  Kbar<sup>-1</sup>, and  $+ (4.5 \pm 0.1) \times 10^{-5}$  Kbar<sup>-1</sup> from resistance and induction measurements, respectively. This latter value is in good agreement with previous observations.<sup>4</sup>

At a second-order transition temperature  $T_0$ , the uniaxial stress effect on  $T_0$  is related to the Young's modulus along the *i*th direction  $E_i$  in the following way<sup>9</sup>

$$\left(\frac{dT_0}{d\sigma_i}\right)^2 = -\left(\frac{\Delta E_i}{E_i^2}\right) \frac{T_0}{\Delta C_p} \ ,$$

where  $\Delta E_i$  and  $\Delta C_p$  are the discontinuities of  $E_i$  and the specific heat at the transition. Based on results of the elastic<sup>10</sup> and specific-heat measure-

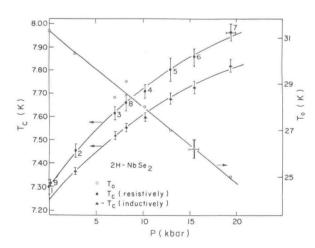


FIG. 1. Pressure dependences of  $T_{\rm \,0}$  and  $T_{\rm \,c}$  of  $2H\textsc{-}{\rm NbSe}_{\rm \,2}.$ 

ments,  $|dT_0/d\sigma_a| = (6 \pm 2) \times 10^{-4} \text{ K bar}^{-1} \text{ for } 2H \text{ -NbSe}_2$ parallel to the layer. Using this value, we deduced the interlayer stress effect  $dT_0/d\sigma_c$  to be  $-(15\pm4)\times10^{-4}$  or  $+(9\pm4)\times10^{-4}$  K bar<sup>-1</sup>, depending on whether  $dT_0/d\sigma_a$  is positive or negative. The corresponding strain derivative of  $T_0$  is  $-5 \times 10^2$ or  $+4 \times 10^2$  K for the "+" or "-" sign of  $dT_0/d\sigma_a$ , based on the estimates of the elastic stiffness constants obtained from neutron and elastic modulus measurements. 11 The interlayer separation thus has a large effect on the CDW formation. The linearly extrapolated critical pressure for the suppression of  $T_0$  to below  $T_c$  is larger than 35 kbar. However, the drastic change of  $dT_c/dP$  at ~35 kbar can still be related to the suppression of CDW to below  $T_c$ , because of the usual nonlinear behavior of To near the critical pressure.12

Recently To of 2H-TaSe, was observed to increase under hydrostatic pressure up to 19 kbar.6 The CDW in 2H-TaSe, becomes commensurate in a first order transition at  $T_d \simeq 90$  K, with a small increase in the CDW amplitude.  $dT_d/dP$  is negative, and the critical pressure for the complete suppression of the commensurate state is ~17 kbar.  $dT_c/dP$  was determined up to 21 kbar to be positive for the superconducting transition of only a small fraction of the sample. The full transition could not be seen, because the experiment could not be conducted at a lower temperature.7 However this positive value is consistent with the general trend in  $dT_c/dP$  across the 2H-TaS<sub>2-x</sub>Se<sub>x</sub> system. Therefore the positive  $dT_c/dP$  in 2H-TaSe, does not seem to be completely accounted for by a possible reduction of the CDW amplitude with pressure due to decreasing  $T_d$ .

The effects of pressure on the CDW temperatures  $T_0$  and  $T_d$ , and on  $T_c$  are known for a number of layer compounds. In general, the three types of phase transitions at  $T_0$ ,  $T_d$ , and  $T_c$  are not all observed in the same layer compound, except in the case of 2H-TaSe2. However, the results in Table I reveal that the pressure coefficients of the three transitions in different compounds at P=1 bar fall into three distinct regions and follow the sequence  $|dT_d/dP| > |dT_0/dP| > |dT_c/dP|$ dP, with about an order of magnitude difference between each. This demonstrates that the influence of pressure on a phase transition depends more on the type of transition involved than on the chemical constituents or the polytype of the layer compound. The larger effect of pressure on  $T_d$ than on To suggests that the incommensuratecommensurate transition at  $T_d$  depends more critically on the band structure of the compound than the normal-incommensurate transition at  $T_0$ .

It is interesting to compare the pressure data on layer compounds with those obtained on unstable isotropic superconductors, as shown in Table II. This is especially true of  $\beta$ -W high- $T_c$  compounds, which show structural instabilities, since it has been suggested that these may be due to CDW instability13,14 (although not yet proven). The magnitude of the pressure dependence of the structural transition temperature  $T_M$  in these compounds is similar to that of  $T_0$  in the layer compounds (see Table I). Since  $T_0$  or  $T_M$  is always higher than  $T_c$ , the relative changes,  $|d \ln T_0/dP|$  or  $|d \ln T_M/dP|$ dP and  $|d \ln T_c/dP|$  thus become roughly comparable to each other. This is consistent with the propositions13,15 that structural changes and superconductivity are just two aspects of the same electronic instability. However, one should also note that, in spite of this resemblance, the CDW formation at  $T_0$  in layer compounds differs from the

TABLE I. Pressure effects on  $T_c$ ,  $T_0$ , and  $T_d$ . For compounds, in which nonlinear pressure behavior exists, the quoted values are for P=1 bar.

Compound	T <sub>c</sub> (K)	$\frac{dT_c/dP}{(10^{-5} \text{ Kbar}^{-1})}$	T <sub>0</sub> (K)	$\frac{dT_0/dP}{(10^{-4} \text{ Kbar}^{-1})}$	$T_d$ (K)	$\frac{d T_d/dP}{(10^{-3} \text{ Kbar}^{-1})}$
2H-NbSe <sub>2</sub>	7.3	+4.95 a	31.3	-3.3 b		a ga bassagan
2H-TaSe2	0.14	+1.3 °	122	+3.5 d	92.5	-2.7 d
2H-TaS2	0.49	+9.3 °	76	-2.2 e	***	la la later alla
1T-TaS2		***	• • • •		190	-9 f
1T-TaSe,				ent of the said	473	-4.7 g
$4Hb-TaS_2$		•••	•••	•••	315	-5.5 h

a Reference 4.

b Present work.

c Reference 7.

d Reference 6.

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